

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of

Atty. Docket

YOURI PONOMAREV

NL 000139

Serial No.

Filed: CONCURRENTLY

SEMICONDUCTOR DEVICE WITH AN INTEGRATED CMOS CIRCUIT WITH MOS TRANSISTORS HAVING SILICON-GERMANIUM ($Si_{1-x}Ge_x$) GATE ELECTRODES, AND METHOD OF MANUFACTURING SAME

Honorable Commissioner of Patents and Trademarks
Washington, D.C. 20231

PRELIMINARY AMENDMENT

Sir:

Prior to calculation of the filing fee and examination, please amend the above-identified application as follows:

IN THE TITLE

Please change the Title to all Capital Letters.

IN THE SPECIFICATION

Page 1, before line 1, insert as a centered heading:

--BACKGROUND OF THE INVENTION--;

Page 2, line 18, insert as a centered heading:

--SUMMARY OF THE INVENTION--;

Page 5, line 4, insert as a centered heading:

--BRIEF DESCRIPTION OF THE DRAWING--;

line 14, insert as a centered heading: